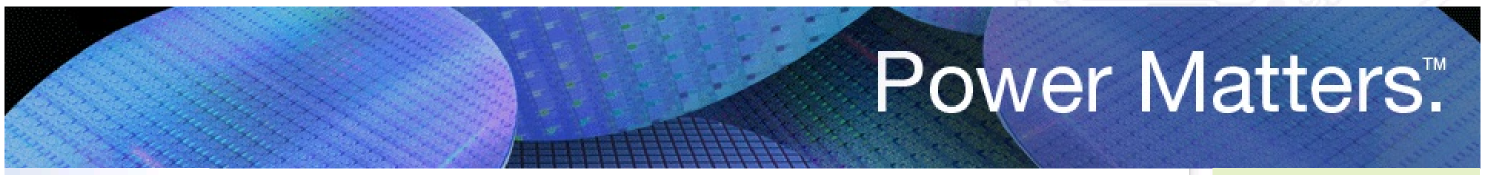

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2N2102 (#22980)

Overview | Diagrams

Electrical Rating	Symbol	Min	Typ	Max	Unit
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$			0.50	V
DC Current Gain	HFE	40.00		120.00	

Maximum Electrical Rating	Symbol	Min	Typ	Max	Unit
Breakdown Voltage, Collector-Base (Emitter Open)	$V_{BR(CBO)}$			120.00	V
Collector Current (dc)	I_C			1.00	A
Collector-Emitter Voltage (Base Open)	V_{CEO}			65.00	V
Emitter-Base Voltage (Collector Open)	V_{EBO}			7.00	V
Power Dissipation, Total	P_T			5.00	W

This part can be found in the following product categories:

- Discretes ▸ Transistors ▸ BJT(BiPolar Junction Transistor) ▸ PNP Transistor
- Non-Radiation Hardened Devices ▸ Transistors ▸ BJT(BiPolar Junction Transistor) ▸ NPN Transistor

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